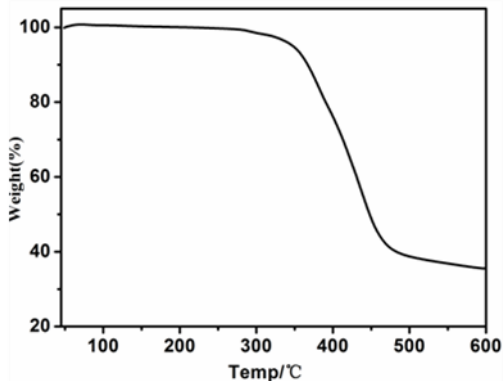


**A Novel Donor-Acceptor Alternating Copolymer Based on Angular-shaped  
Benzo[2,1-b:3,4-b']diselenophene for Bulk Heterojunction Solar Cells**

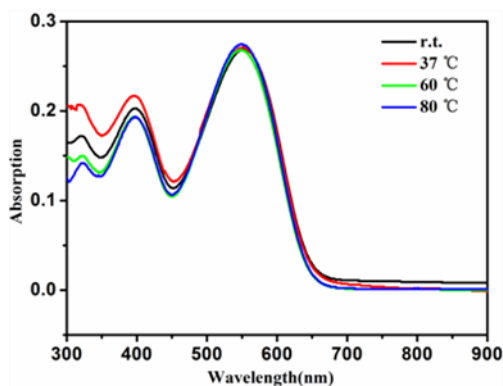
Youyu Jiang, Mingyan Yang, Xuan Huang, Jianhong Gao, Chun Zhan, Shengqiang

Xiao\*

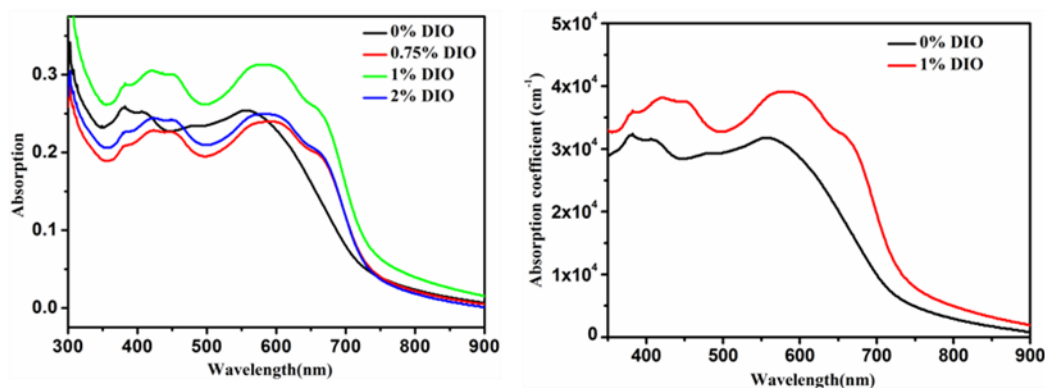
State Key Laboratory of Advanced Technology for Materials Synthesis and  
Processing, WUT-USG Joint Laboratory of Advanced Optoelectronic Materials  
and Devices, Wuhan 430070, P. R. China



**Figure S1.** TGA curve of **PBDSe-DTBT** at a heating rate of  $10\text{ }^{\circ}\text{C min}^{-1}$  under nitrogen flow.



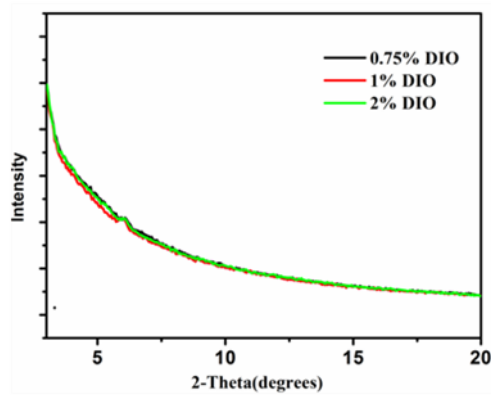
**Figure S2.** Absorption spectra of **PBDSe-DTBT** in *o*-DCB solutions at different temperature.



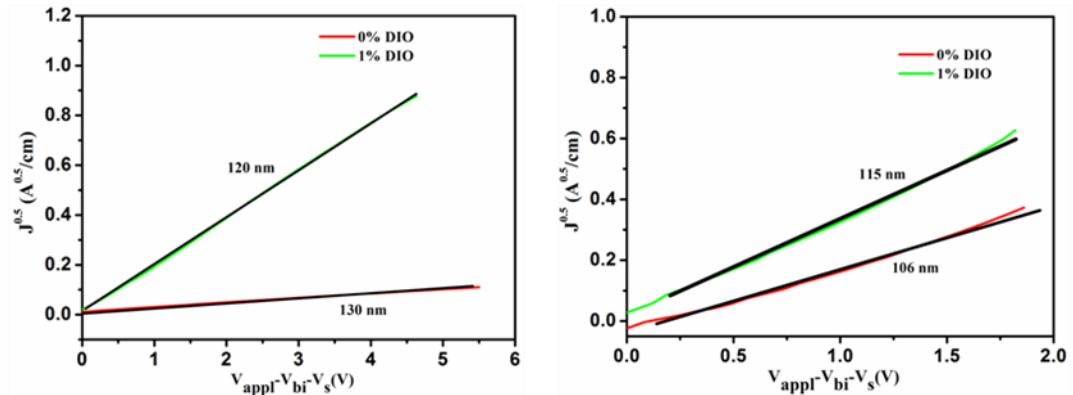
**Figure S3.** Absorption spectra of **PBDSe-DTBT**:  $\text{PC}_{71}\text{BM}$  blend films with different amounts of DIO (left), and absorption coefficients of blend films without DIO and with 1% DIO under optimized device conditions.

**Table S1** Photovoltaic properties of the various ratio of **PBDSe-DTBT**: $\text{PC}_{71}\text{BM}$  BHJs at different blend film thickness with different amounts of DIO additive.

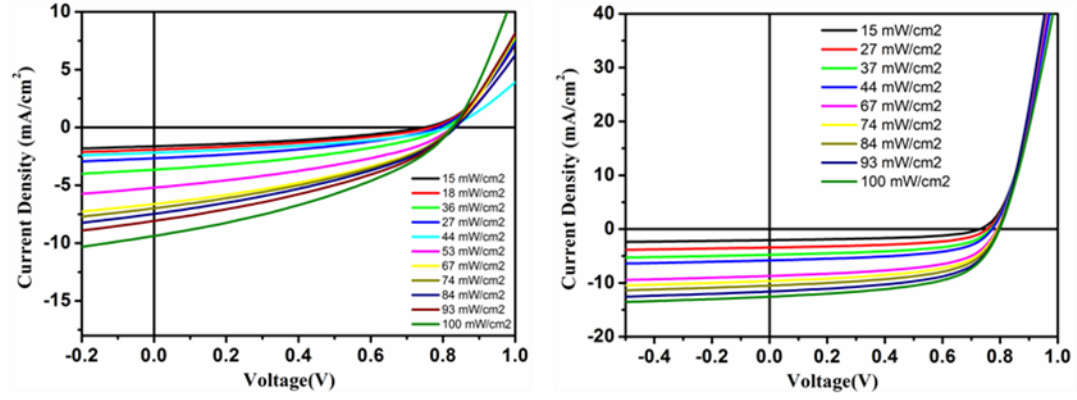
<b>PBDSe-DTBT</b>						
<b>:PC<sub>71</sub>BM</b>	<b>DIO</b>	<b><i>d</i></b>	<b><i>V</i><sub>oc</sub></b>	<b><i>J</i><sub>sc</sub></b>	<b><i>FF</i></b>	<b>PCE</b>
(weight ratio)	(% v/v)	(nm)	(V)	(mA cm <sup>-2</sup> )		(%)
1:0.8	0	90	0.75 ± 0.02	7.78 ± 0.26	0.33 ± 0.01	1.9 ± 0.1
1:1	0	80	0.82 ± 0.01	8.90 ± 0.45	0.37 ± 0.01	2.7 ± 0.1
1:1.5	0	75	0.77 ± 0.02	8.02 ± 0.66	0.36 ± 0.01	2.2 ± 0.2
1:2	0	77	0.82 ± 0.01	8.12 ± 0.53	0.33 ± 0.01	2.2 ± 0.1
	0.75	70	0.80 ± 0.01	8.44 ± 0.43	0.52 ± 0.01	3.5 ± 0.2
	1	74	0.80 ± 0.01	12.30 ± 0.35	0.57 ± 0.01	5.6 ± 0.2
1:1	1.25	76	0.80 ± 0.01	11.38 ± 0.71	0.56 ± 0.01	5.1 ± 0.3
	1.5	74	0.78 ± 0.01	10.66 ± 0.69	0.56 ± 0.01	4.7 ± 0.3
	2	78	0.78 ± 0.01	10.93 ± 0.39	0.56 ± 0.01	4.8 ± 0.1



**Figure S4.** Out-of-plane X-ray profile spectra of pristine **PBDSe-DTBT** and BHJ blend films.



**Figure S5.**  $J^{0.5}$  vs  $V_{\text{appl}}$  plots for hole only devices of ITO/PEDOT: PSS (40 nm)/polymers: PC<sub>71</sub>BM /Pd(50 nm) (left) and electron only devices of glass/Al(80 nm)/PBDSe-DTBT: PC<sub>71</sub>BM/ Ca(20 nm)/Al(80 nm)



**Figure S6.** J-V characteristics of PBDSe-DTBT: PC<sub>71</sub>BM solar cells with 0% DIO (left) and 1% DIO (right) under various light intensities.